

Features

- Wide Power Supply Range, 3.0 V to 5.5 V
- Fast Read Access Time - 120 ns
- Compatible with JEDEC Standard AT27C256R
- Low Power 3.3-Volt CMOS Operation
 - 20 μ A max. Standby
 - 29 mW max. Active at 5 MHz for $V_{CC} = 3.6$ V
 - 110 mW max. Active at 5 MHz for $V_{CC} = 5.5$ V
- Wide Selection of JEDEC Standard Packages
 - 28-Lead 600-mil PDIP and Cerdip
 - 32-Pad PLCC and LCC
 - 28-Lead TSOP and SOIC
- High Reliability CMOS Technology
 - 2000 V ESD Protection
 - 200 mA Latchup Immunity
- Rapid Programming - 100 μ s/byte (typical)
- Two-line Control
- CMOS and TTL Compatible Inputs and Outputs
- Integrated Product Identification Code
- Commercial and Industrial Temperature Ranges

Description

The AT27LV256R chip is a low power, low voltage 262,144 bit ultraviolet erasable and electrically programmable read only memory (EPROM) organized as 32K x 8 bits. It requires only one supply in the range of 3.0 to 5.5 V in normal read mode operation, making it ideal for portable systems.

With a typical power draw of only 10 mW at 1 MHz and V_{CC} at 3.3 V, the AT27LV256R draws less than one-fifth the power of a standard 5-V EPROM. Standby mode supply current is typically less than 1 μ A at 3.3 V.

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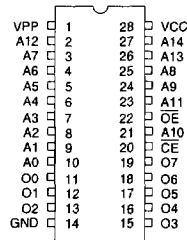
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256K (32K x 8)
Low Voltage
UV
Erasable
CMOS
EPROM

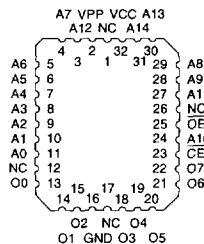
Pin Configurations

Pin Name	Function
A0-A14	Addresses
O0-O7	Outputs
CE	Chip Enable
OE	Output Enable
NC	No Connect

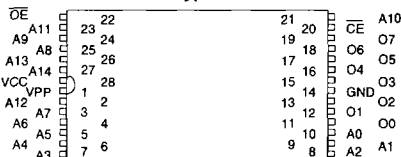
CDIP, PDIP, SOIC Top View



LCC, PLCC Top View



TSOP Top View
Type 1



Note: PLCC Package Pins 1 and 17 are DON'T CONNECT





Description (Continued)

The AT27LV256R comes in a choice of industry standard JEDEC-approved packages, including: one-time programmable (OTP) plastic PDIP, PLCC, SOIC, and TSOP, as well as windowed ceramic Cerdip and LCC. All devices feature two-line control (\overline{CE} , \overline{OE}) to give designers the flexibility to prevent bus contention.

The AT27LV256R operating with V_{CC} at 3.0 V produces TTL level outputs that are compatible with standard TTL logic devices operating at $V_{CC} = 5.0$ V.

Atmel's 27LV256R has additional features to ensure high quality and efficient production use. The Rapid Programming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100 μ s/byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27LV256R programs identically as an AT27C256R.

Erasure Characteristics

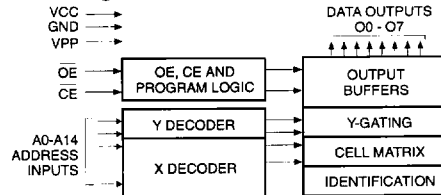
The entire memory array of the AT27LV256R is erased (all outputs read as V_{OH}) after exposure to ultraviolet light at a wavelength of 2537 Å. Complete erasure is assured after a minimum of 20 minutes exposure using 12,000 μ W/cm² intensity lamps spaced one inch away from the chip. Minimum erase time for lamps at other intensity ratings can be calculated from the minimum integrated erasure dose of 15 W·sec/cm². To prevent unintentional erasure, an opaque label is recommended to cover the clear window on any UV erasable EPROM which will be subjected to continuous fluorescent indoor lighting or sunlight.

Operating Modes

Mode \ Pin	\overline{CE}	\overline{OE}	Ai	V _{PP}	V _{CC}	Outputs
Read	V _{IL}	V _{IL}	Ai	V _{CC}	V _{CC}	DOUT
Output Disable	V _{IL}	V _{IH}	X ⁽¹⁾	V _{CC}	V _{CC}	High Z
Standby	V _{IH}	X	X	V _{CC}	V _{CC}	High Z
Rapid Program ⁽²⁾	V _{IL}	V _{IH}	Ai	V _{PP}	V _{CC}	DIN
PGM Verify ⁽²⁾	X	V _{IL}	Ai	V _{PP}	V _{CC} ⁽²⁾	DOUT
Optional PGM Verify ⁽²⁾	V _{IL}	V _{IL}	Ai	V _{CC}	V _{CC} ⁽²⁾	DOUT
PGM Inhibit ⁽²⁾	V _{IH}	V _{IH}	X	V _{PP}	V _{CC} ⁽²⁾	High Z
Product Identification ^{(2),(4)}	V _{IL}	V _{IL}	A9=V _H ⁽³⁾ A0=V _{IH} or V _{IL} A1-A14=V _{IL}	V _{CC}	V _{CC} ⁽²⁾	Identification Code

- Notes:
1. X can be V_{IL} or V_{IH}.
 2. Refer to Programming characteristics. Programming modes require V_{CC} > 4.5 V.
 3. V_H = 12.0 ± 0.5 V.
 4. Two identifier bytes may be selected. All Ai inputs are

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias	-40°C to +85°C
Storage Temperature.....	-65°C to +125°C
Voltage on Any Pin with Respect to Ground.....	-2.0 V to +7.0 V ⁽¹⁾
Voltage on A9 with Respect to Ground	-2.0 V to +14.0 V ⁽¹⁾
V _{PP} Supply Voltage with Respect to Ground.....	-2.0 V to +14.0 V ⁽¹⁾
Integrated UV Erase Dose.....	7258 W·sec/cm ²

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


Notes:

1. Minimum voltage is -0.6 V dc which may undershoot to -2.0 V for pulses of less than 20 ns. Maximum output pin voltage is V_{CC} + 0.75 V dc which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0 V for pulses of less than 20 ns.

held low (V_{IL}), except A9 which is set to V_H and A0 which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.

D.C. and A.C. Operating Conditions for Read Operation

AT27LV256R					
		-12	-15	-20	-25
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
V _{CC} Power Supply		3.0 V to 5.5 V	3.0 V to 5.5 V	3.0 V to 5.5 V	3.0 V to 5.5 V

 = Advance Information

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D.C. and Operating Characteristics for Read Operation

(V_{CC} = 3.0 V to 5.5 V unless otherwise specified)


Symbol	Parameter	Condition	Min	Max	Units
I _{LI}	Input Load Current	V _{IN} = 0 V to V _{CC}		±1	μA
I _{LO}	Output Leakage Current	V _{OUT} = 0 V to V _{CC}		±5	μA
I _{PP1} ⁽²⁾	V _{PP} ⁽¹⁾ Read/Standby Current	V _{PP} = V _{CC}		10	μA
I _{SB}	V _{CC} ⁽¹⁾ Standby Current	I _{SB1} (CMOS), $\overline{CE} = V_{CC} \pm 0.3$ V	V _{CC} = 3.6 V	20	μA
			V _{CC} = 5.5 V	100	μA
		I _{SB2} (TTL), $\overline{CE} = 2.0$ to V _{CC} + 0.5 V	V _{CC} = 3.6 V	100	μA
			V _{CC} = 5.5 V	1	mA
I _{CC}	V _{CC} Active Current	I _{CC1} f = 5 MHz, I _{OUT} = 0 mA, $\overline{CE} = V_{IL}$, V _{CC} = 3.6 V	Com.	8	mA
			Ind.	10	mA
		I _{CC2} f = 5 MHz, I _{OUT} = 0 mA, $\overline{CE} = V_{IL}$, V _{CC} = 5.5 V	Com.	20	mA
			Ind.	25	mA
V _{IL}	Input Low Voltage		-0.6	0.8	V
V _{IH}	Input High Voltage		2.0	V _{CC} +0.5	V
V _{OL}	Output Low Voltage	I _{OL} = 2.0 mA		.4	V
		I _{OL} = 100 μA		.2	V
V _{OH}	Output High Voltage	I _{OH} = -2.0 mA	2.4		V
		I _{OH} = -100 μA	V _{CC} -0.2		V

Notes: 1. V_{CC} must be applied simultaneously or before V_{PP}, and removed simultaneously or after V_{PP}. 2. V_{PP} may be connected directly to V_{CC}, except during programming. The supply current would then be the sum of I_{CC} and I_{PP}.

A.C. Characteristics for Read Operation (V_{CC} = 3.0V to 5.5V)

			AT27LV256R								
			-12		-15		-20		-25		Units
Symbol	Parameter	Condition	Min	Max	Min	Max	Min	Max	Min	Max	
t _{ACC} ⁽³⁾	Address to Output Delay	$\overline{CE} = \overline{OE} = V_{IL}$	Com.	120	150	200	250	ns			
			Ind.	120	150	200	250	ns			
t _{CE} ⁽²⁾	\overline{CE} to Output Delay	$\overline{OE} = V_{IL}$		120	150	200	250	ns			
t _{OE} ^(2,3)	\overline{OE} to Output Delay	$\overline{CE} = V_{IL}$		50	60	70	100	ns			
t _{DF} ^(4,5)	\overline{OE} or \overline{CE} High to Output Float			40	50	50	50	ns			
t _{OH}	Output Hold from Address, \overline{CE} or \overline{OE} , whichever occurred first		0		0		0		0		ns

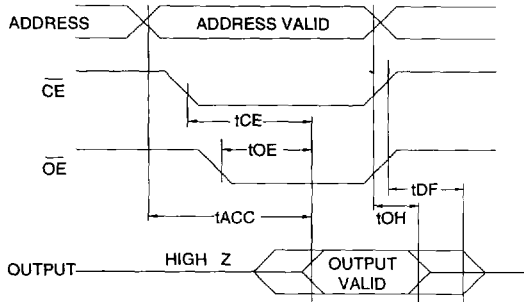
Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.

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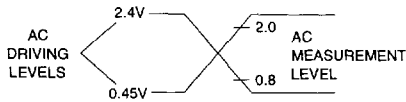
A.C. Waveforms for Read Operation ⁽¹⁾



Notes:

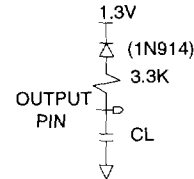
1. Timing measurement references are 0.8 V and 2.0 V. Input AC driving levels are 0.45 V and 2.4 V. See Input Test Waveforms and Measurement Levels.
2. \overline{OE} may be delayed up to $t_{CE}-t_{OE}$ after the falling edge of \overline{CE} without impact on t_{CE} .
3. \overline{OE} may be delayed up to $t_{ACC}-t_{OE}$ after the address is valid without impact on t_{ACC} .
4. This parameter is only sampled and is not 100% tested.
5. Output float is defined as the point when data is no longer driven.

Input Test Waveforms and Measurement Levels



$t_r, t_f < 20$ ns (10% to 90%)

Output Test Load



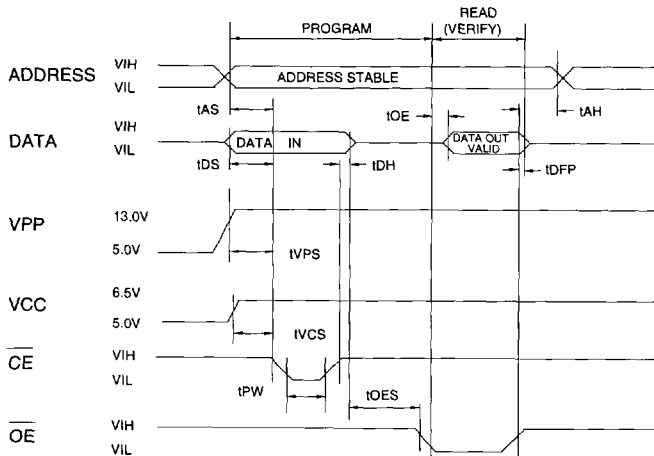
Note: $C_L = 100$ pF including jig capacitance.

Pin Capacitance ($f = 1$ MHz, $T = 25^\circ\text{C}$) ⁽¹⁾

	Typ	Max	Units	Conditions
C_{IN}	4	8	pF	$V_{IN} = 0$ V
C_{OUT}	8	12	pF	$V_{OUT} = 0$ V

Notes: 1. Typical values for 5-V supply voltage. This parameter is only sampled and is not 100% tested.

Programming Waveforms ⁽¹⁾



Notes:

1. The Input Timing Reference is 0.8 V for V_{IL} and 2.0 V for V_{IH} .
2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.
3. When programming the AT27LV256R a 0.1- μF capacitor is required across V_{PP} and ground to suppress spurious voltage transients.

D.C. Programming Characteristics

$T_A = 25 \pm 5^\circ\text{C}$, $V_{CC} = 6.5 \pm 0.25\text{ V}$, $V_{PP} = 13.0 \pm 0.25\text{ V}$

Sym- bol	Parameter	Test Conditions	Limits	
			Min	Max - Units
I _{LI}	Input Load Current	$V_{IN} = V_{IL}, V_{IH}$	10	μA
V _{IL}	Input Low Level	(All Inputs)	-0.6	0.8 V
V _{IH}	Input High Level		2.0	$V_{CC} + 1$ V
V _{OL}	Output Low Volt.	$I_{OL} = 2.1\text{ mA}$.45	V
V _{OH}	Output High Volt.	$I_{OH} = 400\ \mu\text{A}$	2.4	V
I _{CC2}	V _{CC} Supply Current (Program and Verify)		25	mA
I _{PP2}	V _{PP} Current	$\overline{CE} = V_{IL}$	25	mA
V _{ID}	A9 Product Identification Voltage		11.5	12.5 V

A.C. Programming Characteristics

$T_A = 25 \pm 5^\circ\text{C}$, $V_{CC} = 6.5 \pm 0.25\text{ V}$, $V_{PP} = 13.0 \pm 0.25\text{ V}$

Sym- bol	Parameter	Test Conditions* (see Note 1)	Limits	
			Min	Max Units
t _{AS}	Address Setup Time		2	μs
t _{OES}	\overline{OE} Setup Time		2	μs
t _{DS}	Data Setup Time		2	μs
t _{AH}	Address Hold Time		0	μs
t _{DH}	Data Hold Time		2	μs
t _{DFP}	\overline{OE} High to Out- put Float Delay	(Note 2)	0	130 ns
t _{VPS}	V _{PP} Setup Time		2	μs
t _{VCS}	V _{CC} Setup Time		2	μs
t _{PW}	\overline{CE} Program Pulse Width	(Note 3)	95	105 μs
t _{OE}	Data Valid from \overline{OE}	(Note 2)		150 ns

*A.C. Conditions of Test:

Input Rise and Fall Times (10% to 90%) 20 ns
 Input Pulse Levels 0.45 V to 2.4 V
 Input Timing Reference Level 0.8 V to 2.0 V
 Output Timing Reference Level 0.8 V to 2.0 V

Notes:

- V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
- This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram.
- Program Pulse width tolerance is 100 $\mu\text{s} \pm 5\%$.

Atmel's 27LV256R Integrated Product Identification Code⁽¹⁾

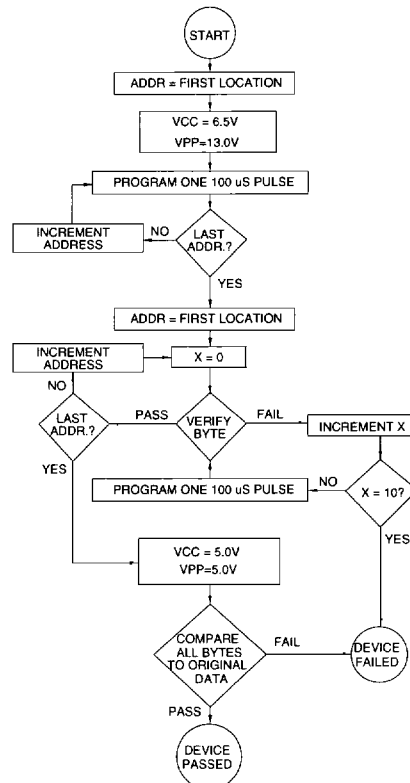
Codes	Pins								Hex Data	
	A0	O7	O6	O5	O4	O3	O2	O1		O0
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	1	0	0	0	1	1	0	0	8C

Note: 1. The AT27LV256R has the same Product Identification Code as the AT27C256R. Both are programming compatible.

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Rapid Programming Algorithm


A 100 μs \overline{CE} pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5 V and V_{PP} is raised to 13.0 V. Each address is first programmed with one 100 μs \overline{CE} pulse without verification. Then a verification/reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100 μs pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked. V_{PP} is then lowered to 5.0 V and V_{CC} to 5.0 V. All bytes are read again and compared with the original data to determine if the device passes or fails.





Ordering Information

t _{ACC} (ns)	I _{CC} (mA) V _{CC} = 3.6 V		Ordering Code	Package	Operation Range
	Active	Standby			
120	8	0.02	AT27LV256R-12DC AT27LV256R-12JC AT27LV256R-12LC AT27LV256R-12PC AT27LV256R-12RC AT27LV256R-12TC	28DW6 32J 32LW 28P6 28R 28T	Commercial (0°C to 70°C)
120	10	0.02	AT27LV256R-12DI AT27LV256R-12JI AT27LV256R-12LI AT27LV256R-12PI AT27LV256R-12RI AT27LV256R-12TI	28DW6 32J 32LW 28P6 28R 28T	Industrial (-40°C to 85°C)
150	8	0.02	AT27LV256R-15DC AT27LV256R-15JC AT27LV256R-15LC AT27LV256R-15PC AT27LV256R-15RC AT27LV256R-15TC	28DW6 32J 32LW 28P6 28R 28T	Commercial (0°C to 70°C)
150	10	0.02	AT27LV256R-15DI AT27LV256R-15JI AT27LV256R-15LI AT27LV256R-15PI AT27LV256R-15RI AT27LV256R-15TI	28DW6 32J 32LW 28P6 28R 28T	Industrial (-40°C to 85°C)
200	8	0.02	AT27LV256R-20DC AT27LV256R-20JC AT27LV256R-20LC AT27LV256R-20PC AT27LV256R-20RC AT27LV256R-20TC	28DW6 32J 32LW 28P6 28R 28T	Commercial (0°C to 70°C)
200	10	0.02	AT27LV256R-20DI AT27LV256R-20JI AT27LV256R-20LI AT27LV256R-20PI AT27LV256R-20RI AT27LV256R-20TI	28DW6 32J 32LW 28P6 28R 28T	Industrial (-40°C to 85°C)

 = Advance Information

Ordering Information

t _{ACC} (ns)	I _{CC} (mA)		Ordering Code	Package	Operation Range
	V _{CC} = 3.6 V				
	Active	Standby			
250	8	0.02	AT27LV256R-25DC AT27LV256R-25JC AT27LV256R-25LC AT27LV256R-25PC AT27LV256R-25RC AT27LV256R-25TC	28DW6 32J 32LW 28P6 28R 28R	Commercial (0°C to 70°C)
250	10	0.02	AT27LV256R-25DI AT27LV256R-25JI AT27LV256R-25LI AT27LV256R-25PI AT27LV256R-25RI AT27LV256R-25TI	28DW6 32J 32LW 28P6 28R 28R	Industrial (-40°C to 85°C)

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Package Type	
28DW6	28 Lead, 0.600" Wide, Windowed, Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier OTP (PLCC)
32LW	32 Pad, Windowed, Ceramic Leadless Chip Carrier (LCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package OTP (PDIP)
28R	28 Lead, 0.330" Wide, Plastic Gull Wing Small Outline OTP (SOIC)
28T	28 Lead, Plastic Thin Small Outline Package OTP (TSOP)